

## **NPN Epitaxial Silicon Transistor**

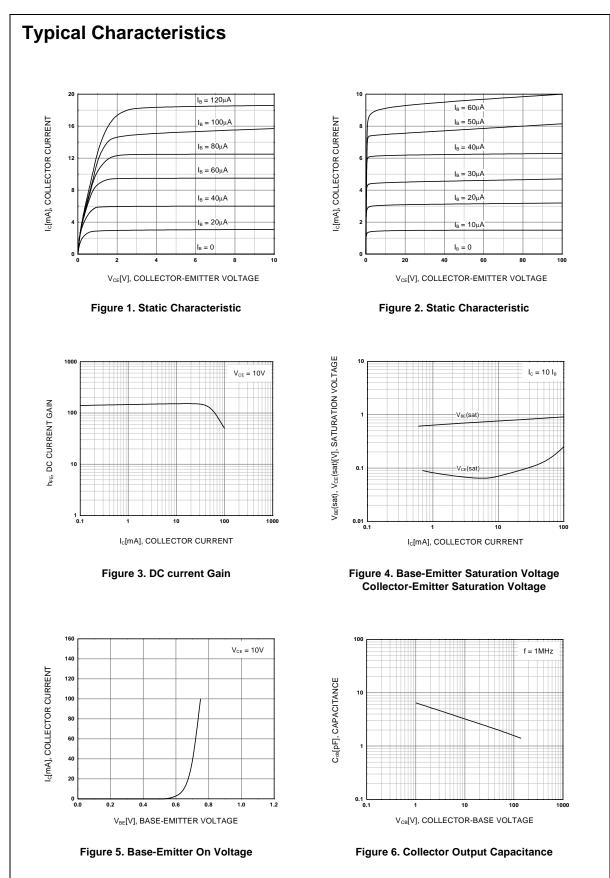
Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	300	V
V <sub>CEO</sub>	Collector-Emitter Voltage	300	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current (DC)	100	mA
I <sub>CP</sub>	Collector Current (Pulse)	200	mA
Pc	Collector Dissipation (T <sub>C</sub> =25°C)	7	W
P <sub>C</sub> P <sub>C</sub>	Collector Dissipation (T <sub>A</sub> =25°C)	1.2	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

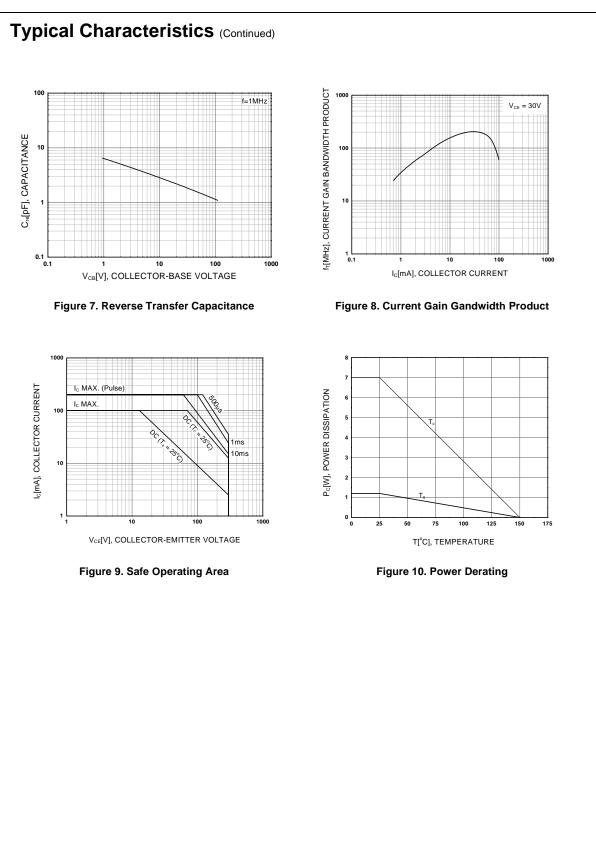
## Electrical Characteristics Tc=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$	300			V
BV <sub>CEO</sub>	Collecto- Emitter Breakdown Voltage	I <sub>C</sub> = 1mA, I <sub>B</sub> = 0	300			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \mu A, I_{\rm C} = 0$	5			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 200V, I_E = 0$			0.1	μA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 4V, I_{C} = 0$			0.1	μA
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 10V, I_{C} = 10mA$	40	24	320	- 60
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 20mA, I <sub>B</sub> = 2mA		24	0.6	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_{\rm C} = 20$ mA, $I_{\rm B} = 2$ mA	1. 2.	N. A	1	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = 30V, I_{C} = 10mA$		150		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 30V, f = 1MHz		2.6		pF
C <sub>re</sub>	Reverse Transfer Capacitance	V <sub>CB</sub> = 30V, f = 1MHz		1.8		pF

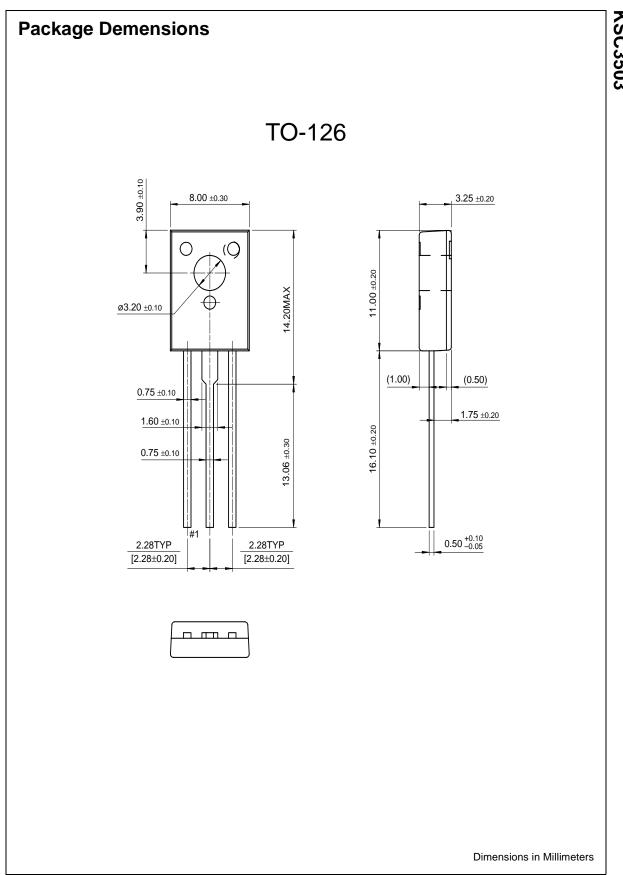
h <sub>FE</sub> Classification				
Classification	С	D	E	F
h <sub>FE</sub>	40 ~ 80	60 ~ 120	100 ~ 200	160 ~ 320



## KSC3503



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